

Description

- ★ Advanced Trench MOSFET Technology
- ★ 100% EAS Guaranteed
- ★ Green Device Available

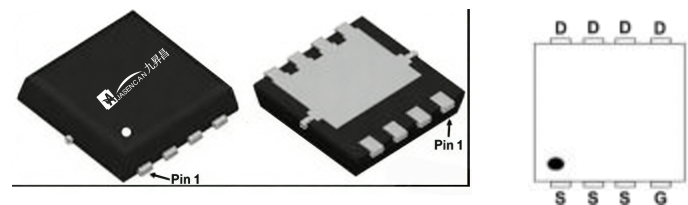
Product Summary

BVDSS	RDSON	ID
-60V	25mΩ	-26A

Applications

- ★ Load Switch.
- ★ Power Management.
- ★ DC/DC Converter.
- ★ LED Backlighting.
- ★ Telecom.

PRPAK3X3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-26	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-16	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-6.8	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-5.4	A
I_{DM}	Pulsed Drain Current ²	-70	A
EAS	Single Pulse Avalanche Energy ³	113	mJ
I_{AS}	Avalanche Current	47.6	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	31.25	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4	$^\circ C/W$

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-12A$	---	20	25	m Ω
		$V_{GS}=-4.5V$, $I_D=-10A$	---	25	33	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	-1.5	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10V$, $I_D=-12A$	---	23	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	7	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V$, $V_{GS}=-4.5V$, $I_D=-12A$	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	6.7	---	
Q_{gd}	Gate-Drain Charge		---	5.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3\Omega$, $I_D=-1A$	---	38	---	ns
T_r	Rise Time		---	23.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	100	---	
T_f	Fall Time		---	6.8	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3635	---	pF
C_{oss}	Output Capacitance		---	224	---	
C_{riss}	Reverse Transfer Capacitance		---	141	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-26	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V$, $V_{GS}=-10V$, $L=0.1\text{mH}$, $I_{AS}=-47.6A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

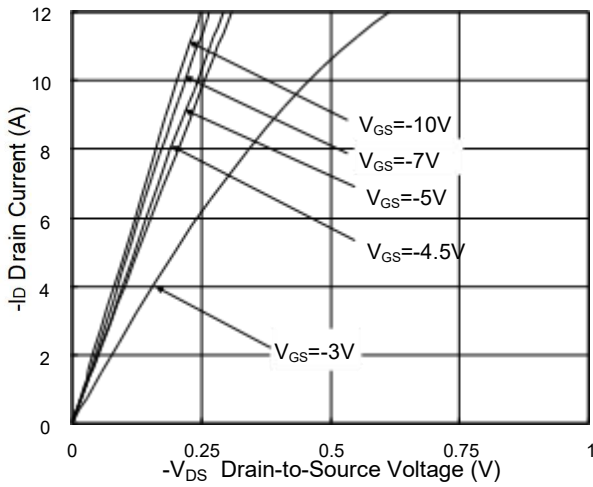


Fig.1 Typical Output Characteristics

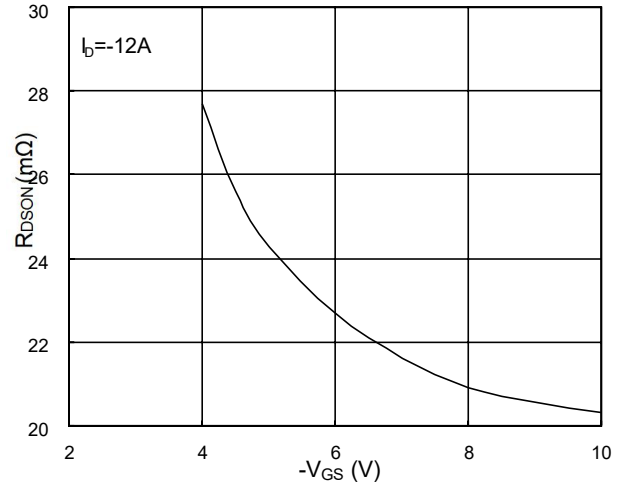


Fig.2 On-Resistance vs G-S Voltage

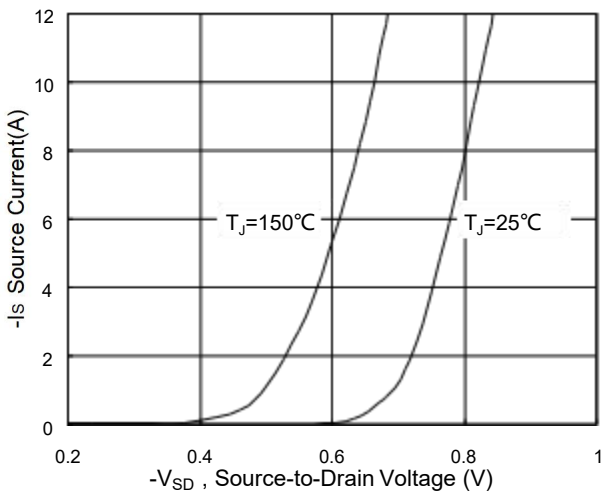


Fig.3 Source Drain Forward Characteristics

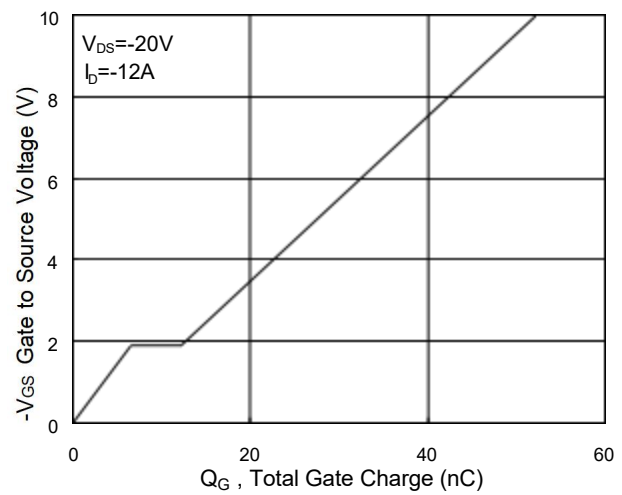


Fig.4 Gate-Charge Characteristics

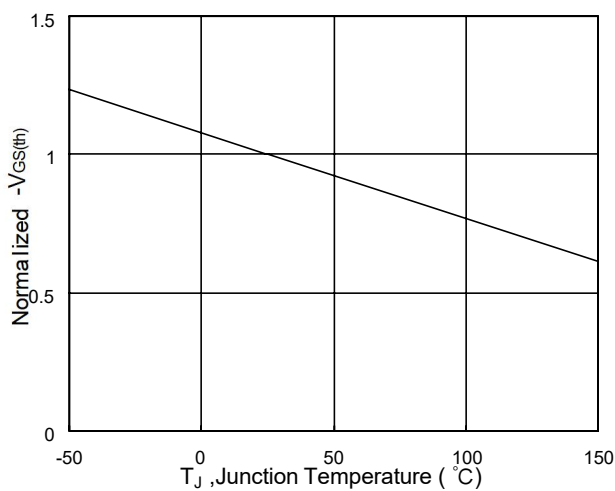


Fig.5 Normalized $V_{GS(th)}$ vs T_J

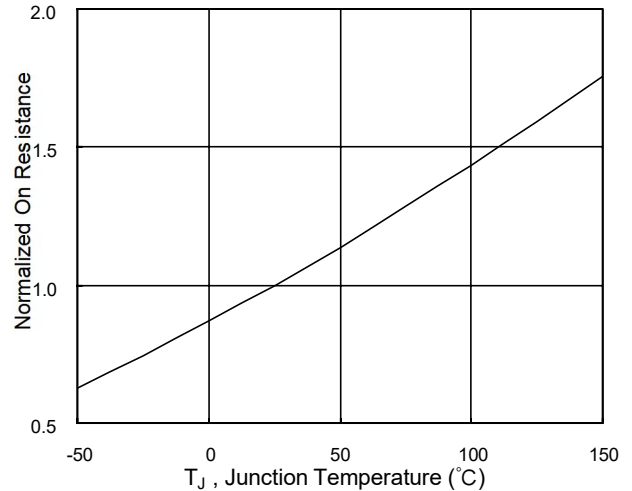


Fig.6 Normalized $R_{DS(on)}$ vs T_J

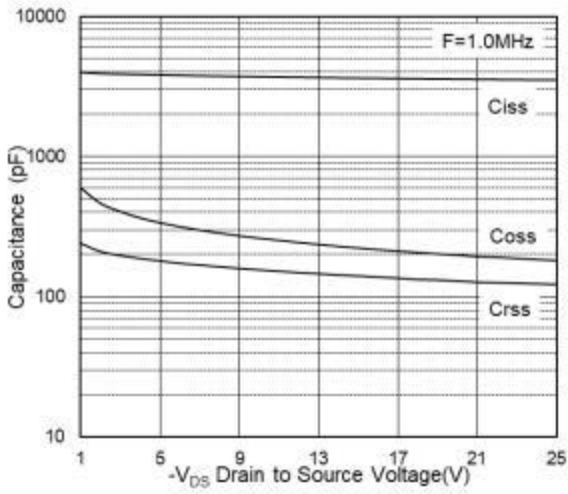


Fig.7 Capacitance

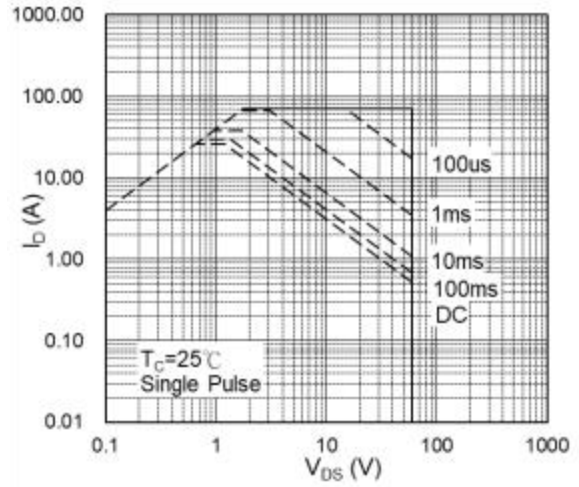


Fig.8 Safe Operating Area

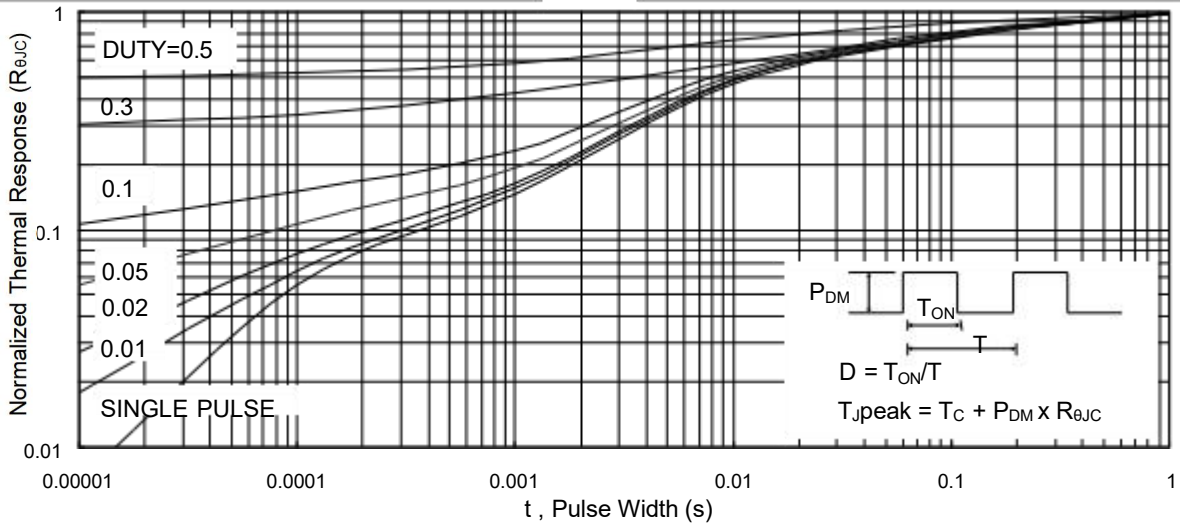


Fig.9 Normalized Maximum Transient Thermal Impedance

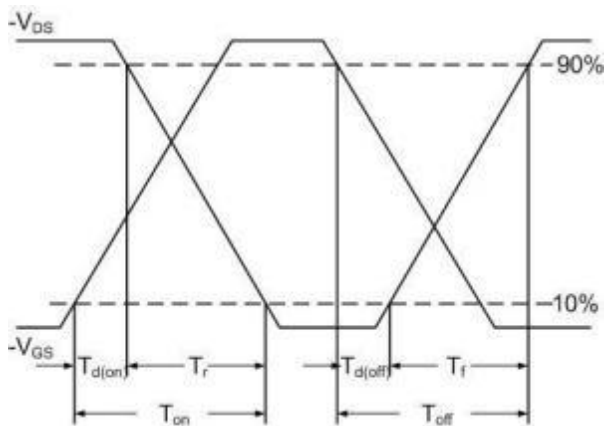


Fig.10 Switching Time Waveform

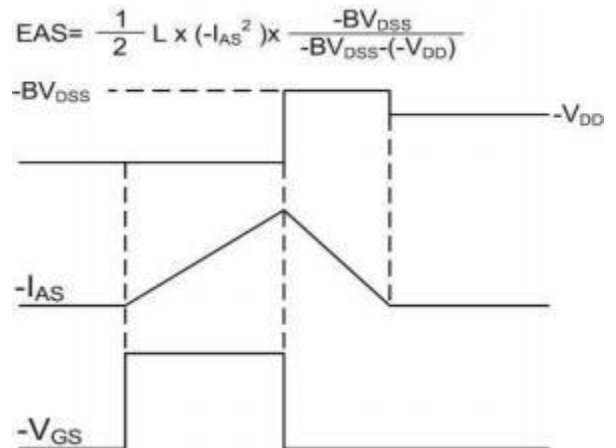
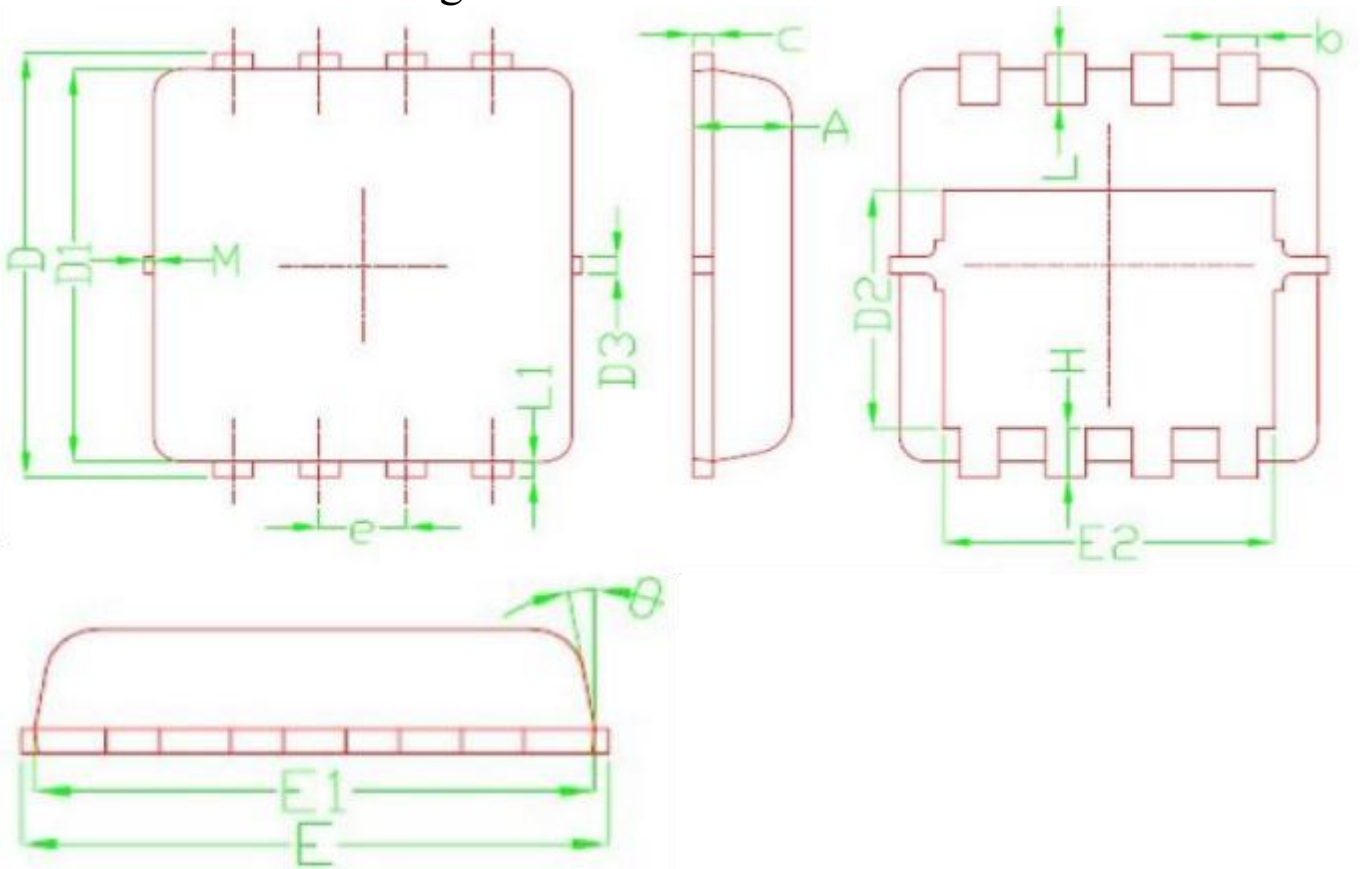


Fig.11 Unclamped Inductive Waveform

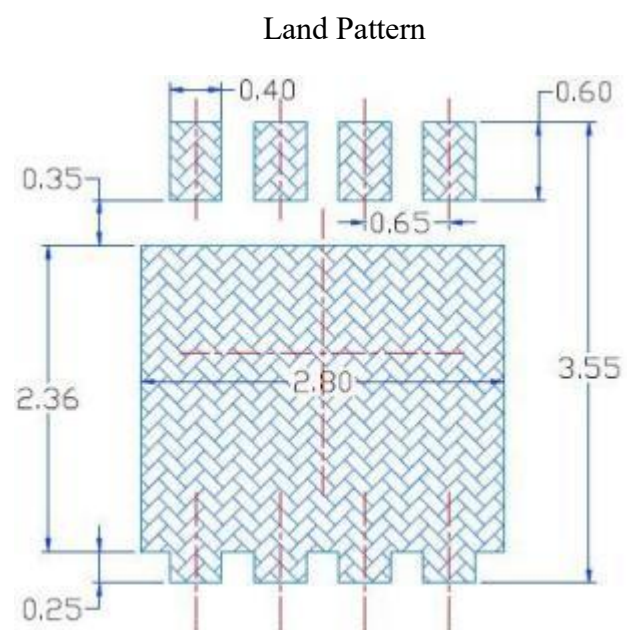
$$EAS = \frac{1}{2} L \times (-I_{AS}^2) \times \frac{-BV_{DSS}}{-BV_{DSS} - (-V_{DD})}$$

PRPAK3x3-8L Package Outline



SYMBOL	MIN	NOM	MAX
A	0.70	----	0.85
b	0.20	----	0.40
c	0.10	----	0.25
D	3.15	----	3.45
D1	2.90	----	3.20
D2	1.54	----	1.98
D3	0.10	0.20	0.30
E	3.15	----	3.45
E1	3.00	----	3.25
E2	2.29	----	2.65
e	0.65 BSC		
H	0.28	----	0.65
g	0°	----	14°
L	0.30	----	0.50
L1	----	0.13	----
M	----	----	0.15

Unit: mm



JSBB 系列 (PRPAK3X3)包装规范

1. 包装方式 Packing Method(Tape and Reel)

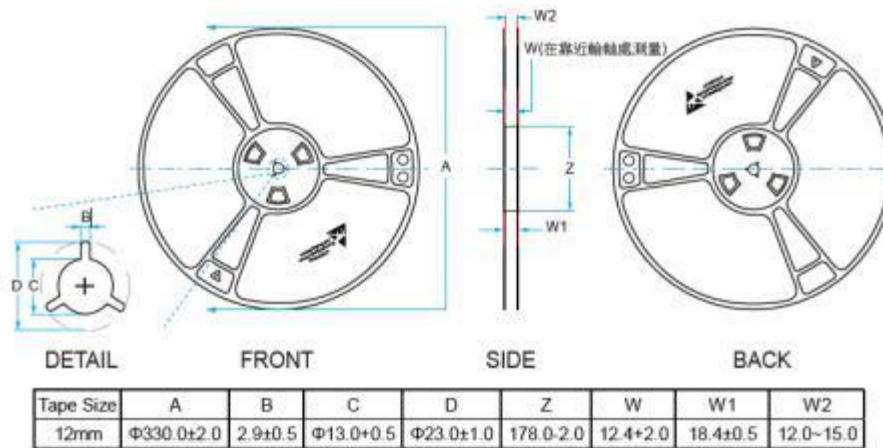
Reel Color : 蓝色 or 黑色
Carrier Tape : 黑色
Cover Tape : 热溶性

Trailer 后(空格) : >300mm
Leader 前(空格) : >500mm

Reel尺寸	卷盘数量	铝箔袋	内盒数量	外箱数量
13吋	3,000pcs	3,000pcs	6,000pcs	36,000 pcs

备注：外箱依各封测厂现有通用外箱做出货，故实际外箱数量会有差异。

1.1 Reel Dimensions



1.2. Carrier Tape Dimensions

